

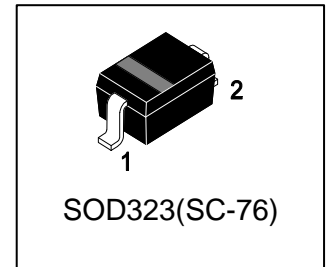
L1SS356T1G

S-L1SS356T1G

Band Switching Diode

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Silicon epitaxial planar
- Small surface mounting type.
- High reliability.
- High frequency switching



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
L1SS356T1G	B	3000/Tape&Reel
L1SS356T3G	B	10000/Tape&Reel

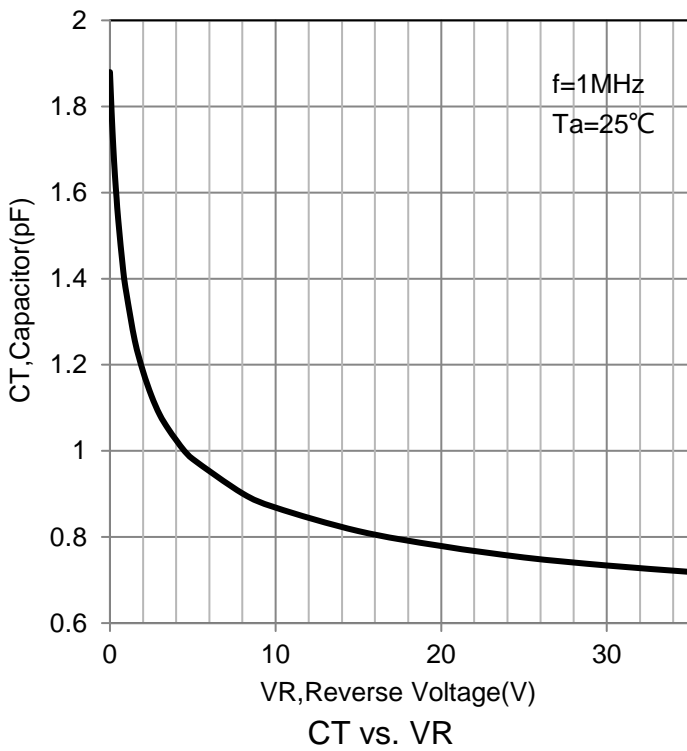
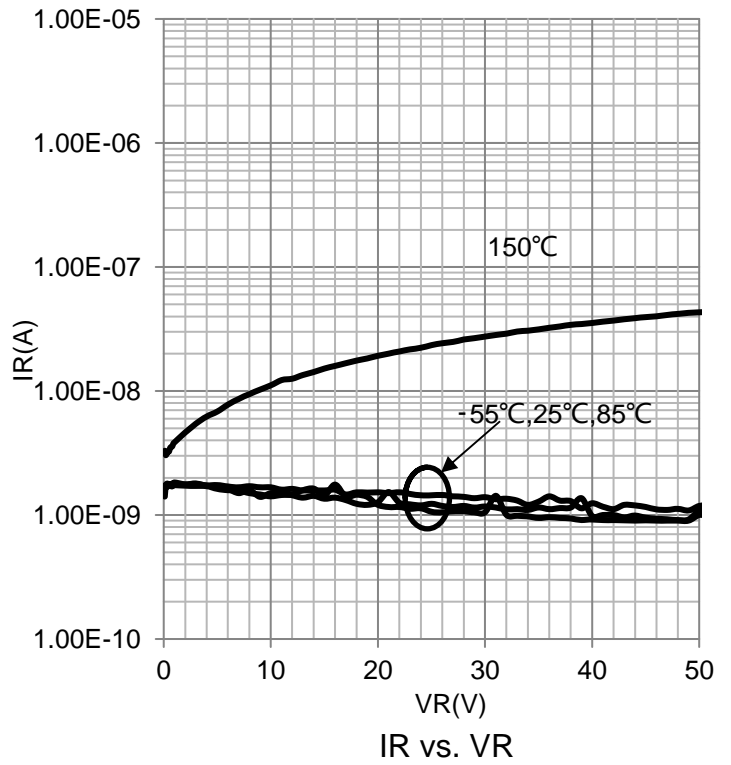
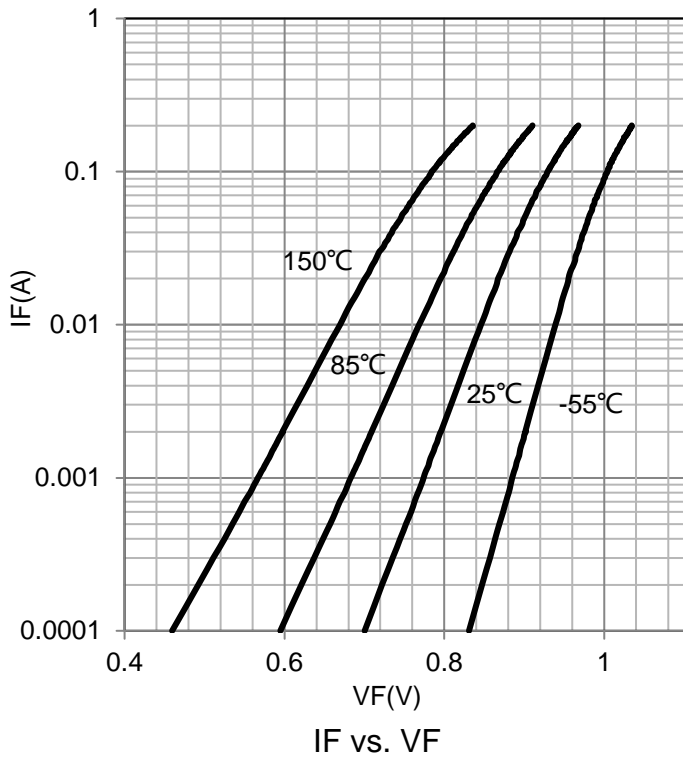
3. MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	VR	35	V
DC forward current	IF	100	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

4. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Forward voltage (IF =10mA)	VF	-	-	1	V
Reverse current (VR =25V)	IR	-	-	10	nA
Capacitance between terminals (VR =6V, f =1MHz)	CT	-	-	1.2	pF
Forward operating resistance (IF =2mA, f =100MHz)	rF	-	-	0.9	Ohm

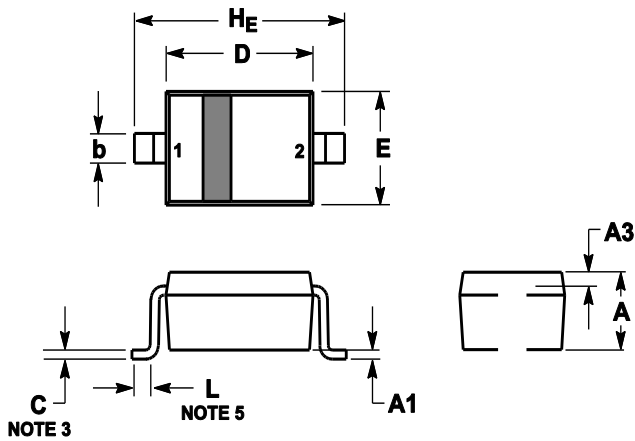
5.ELECTRICAL CHARACTERISTICS CURVES



6. OUTLINE AND DIMENSIONS

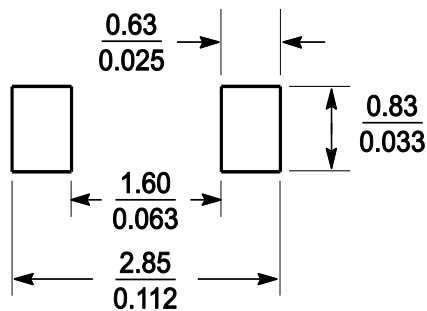
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.8	0.9	1	0.031	0.035	0.04
A1	0	0.05	0.1	0	0.002	0.004
A3	0.15REF			0.006REF		
b	0.25	0.32	0.4	0.01	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.6	1.7	1.8	0.062	0.066	0.07
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
HE	2.3	2.5	2.7	0.09	0.098	0.105

7. SOLDERING FOOTPRINT



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)